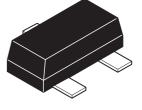


ZXMP2120FF 200V SOT23F P-channel enhancement mode MOSFET

Summary

V _{(BR)DSS}	R _{DS(on)} (Ω)	I _D (mA)	
-200	28 @ V _{GS} = -10V	-137	



Description

This 200V enhancement mode P-channel MOSFET provides users with a competitive specification offering efficient power handling capability, high impedance and freedom from thermal runaway and thermally induced secondary breakdown.

Applications benefiting from this device include a variety of telecom and general high voltage circuits.

Features

- High voltage
- Low on-resistance
- · Fast switching speed
- Low gate drive
- Low threshold
- SOT23 FLAT package

Applications

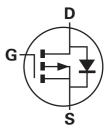
Active clamping of primary side MOSFETs in 48 volt DC-DC converters

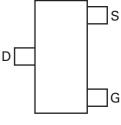
Ordering information

Device	Reel size	Tape width	Quantity
	(inches)	(mm)	per reel
ZXMP2120FFTA	7	8	3,000

Device marking

1C4





Top view

1

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Drain-source voltage	V _{DSS}	-200	V
Gate-source voltage	V _{GS}	± 20	V
Continuous drain current @ V _{GS} = 10V; T _{amb} =25°C ^(a)	Ι _D	-137	mA
Pulsed drain current ^(c)	I _{DM}	-0.8	А
Pulsed source current (body diode) ^(c)	I _{SM}	-0.8	А
Power dissipation at T _{amb} =25°C ^(a)	PD	1	W
Linear derating factor		8	mW/°C
Power dissapation at T _{amb} =25°C ^(b)	P _D	1.5	W
Linear derating factor		12.3	mW/°C
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	R_{\ThetaJA}	125	°C/W
Junction to ambient ^(b)	R_{\ThetaJA}	81	°C/W

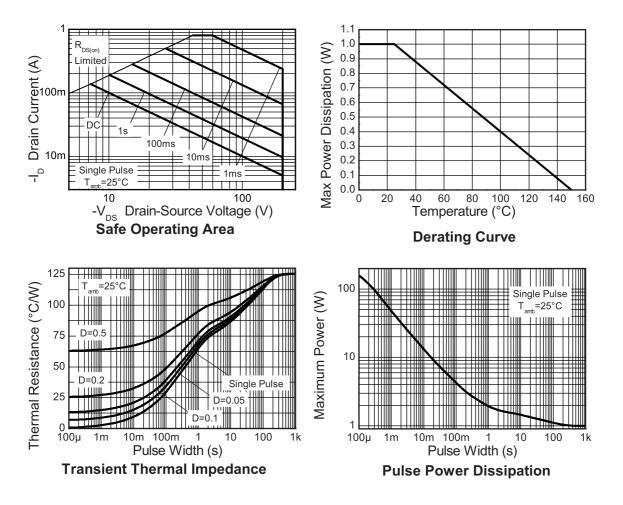
NOTES:

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) For a device surface mounted on FR4 pcb measured at t ${\leq}5$ sec.

(c) Repetitive rating - 25mm x 25mm FR4 PCB, D=0.02, pulse width 300μs - pulse width limited by maximum junction temperature.

Thermal characteristics



Parameter	Symbol	Min.	Max.	Unit	Conditions
Static	1		1		
Drain-source breakdown voltage	V _{(BR)DSS}	-200		V	I _D = 1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}		-10	μA	V _{DS} = -200V, V _{GS} =0V
			-100	μA	V _{DS} = -160V, V _{GS} =0V, T=125C ^(‡)
Gate-body leakage	I _{GSS}		20	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Gate-source threshold voltage	V _{GS(th)}	-1.5	-3.5	V	$I_D = 250 \mu A, V_{DS} = V_{GS}$
Static drain-source on-state resistance ^(*)	R _{DS(on)}		28	Ω	V _{GS} = -10V, I _D = -150mA
On-state drain current ^(*)	I _{D(on)}	-300		mA	V _{DS} = -25V, V _{GS} =-10V
Forward transconductance ^{(*) (‡)}	9 _{fs}	50		mS	V _{DS} = -25V, I _D = -150mA
Dynamic ^(‡)			•		
Input capacitance	C _{iss}		100	pF	V _{DS} = -25V, V _{GS} =0V
Output capacitance	C _{oss}		25	pF	f=1MHz
Reverse transfer capacitance	C _{rss}		7	pF	
Switching ^{(†) (‡)}	•			1	
Turn-on-delay time	t _{d(on)}		7	ns	V _{DD} = -25V, V _{GS} = -10V
Rise time	t _r		15	ns	I _D = -150mA
Turn-off delay time	t _{d(off)}		12	ns	$R_{SOURCE} \approx 50\Omega$
Fall time	t _f		15	ns	

Electrical characteristics (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

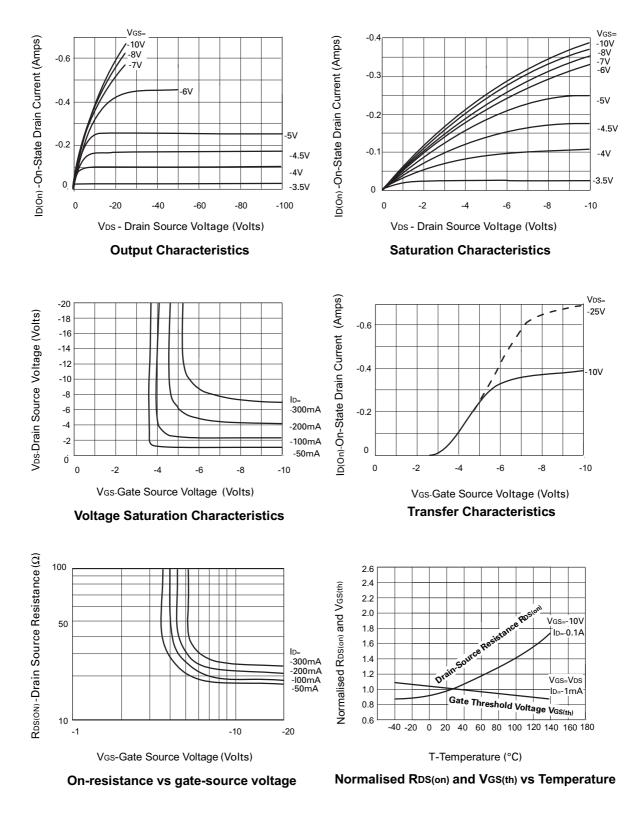
NOTES:

(*) Measured under pulsed conditions. Pulse width ${\leq}300\mu s;$ duty cycle ${\leq}2\%.$

(†) Switching characteristics are independent of operating junction temperature.

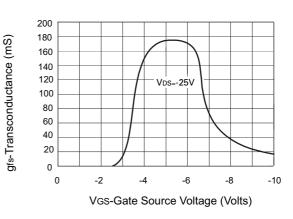
(‡) For design aid only, not subject to production testing.

Typical charateristics



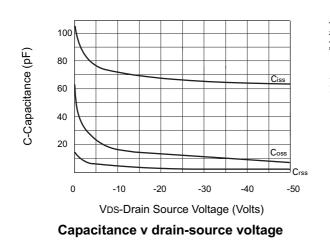
200 180 gfs-Transconductance (mS) VDS=-25V 160 140 120 100 80 60 40 20 0 0 -0.2 -0.4 -0.8 -0.6 ID- Drain Current (Amps)

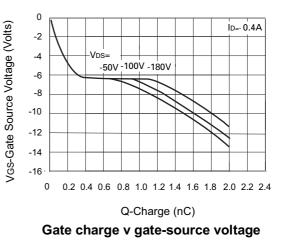
Typical characteristics



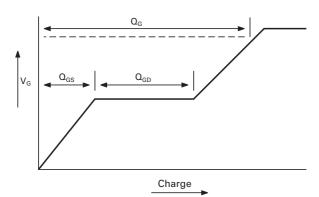
Transconductance v drain current Tr



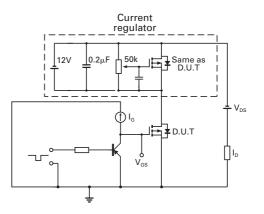




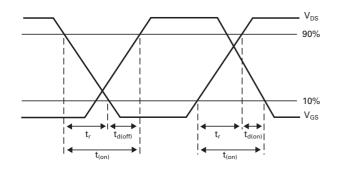
Typical characteristics



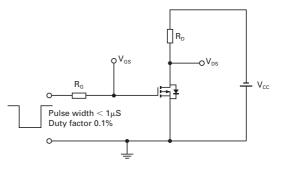
Basic gate charge waveform



Gate charge test circuit



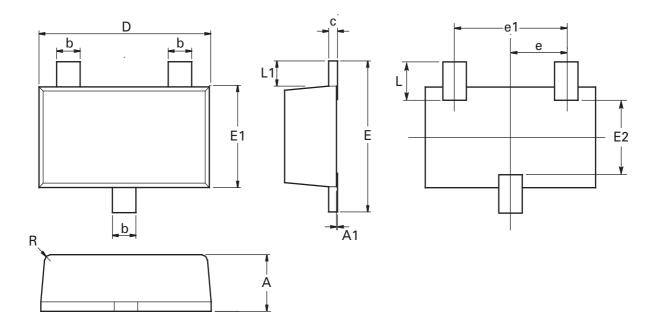
Switching time waveforms



Switching time test circuit

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Package outline - SOT23F



Dim.	Millim	Millimeters Inches		Dim.	Millimeters		Inches		
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
A	0.80	1.00	0.0315	0.0394	E	2.30	2.50	0.0906	0.0984
A1	0.00	0.10	0.00	0.0043	E1	1.50	1.70	0.0590	0.0669
b	0.35	0.45	0.0153	0.0161	E2	1.10	1.26	0.0433	0.0496
С	0.10	0.20	0.0043	0.0079	L	0.48	0.68	0.0189	0.0268
D	2.80	3.00	0.1102	0.1181	L1	0.30	0.50	0.0153	0.0161
е	0.95	ref	0.037	74 ref	R	0.05	0.15	0.0019	0.0059
e1	1.80	2.00	0.0709	0.0787	0	0°	12°	0°	12°

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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